MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PLED

74HC4051-MS

产品规格手册



semicond 概述

MSKSEMI

74HC4051-MS 是一款采用先进 CMOS 技术设计的单个 8 通道多路复用器。是一个单刀八掷配置形式的模拟 开 关。 具有三个二进制通道控制输入(A、B、C)以及 一个使能输入 INH。二进制输入信号,控制 8 个通道 中的 一个通道开启,其余通道关闭。

特征

- 低输入电流: IIN ≤1uA, @VIN=VDD-VSS=15V, Ta=25℃
- 低静态功耗: IDD=0.2uA(典型)@VDD-VSS=15V, Ta=25℃
- 低通电阻: 60Q (典型)@VDD-VSS=VDD-VEE=15V, Ta=25℃
- 通道漏电流: ±100nA(典型) @VDD-VEE=15V
- 宽工作电压 VDD-VSS 范围: 3V~15V
- 先断后通切换消除了通道重迭开启
- 单刀八掷配置形式的模拟开关

产品用途

- 模拟和数字多路复用与解复用
- 数字寻址信号的逻辑电平转换
- 信号选通
- 其它应用领域

参考信息

封装图	脚位信	息
William Constant	CHANNELS $\begin{cases} 4 & 1 \\ 6 & 2 \\ COM OUT/IN & 3 \\ CHANNELS \\ IN/OUT \end{cases} \begin{cases} 7 & 4 \\ 5 & 5 \\ 5 & 5 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 \\ 100 $	16 V _{DD} 15 2 14 1 13 0 12 3 11 A 10 B 9 C
SOP-16	管脚巧	力能定义

封装形式和管脚功能定义

管脚序号	管脚定义	说明	管脚序号	管脚定义	说明
1	4	4 通道	16	VDD	电源正
2	6	6 通道	15	2	2 通道
3	COM OUT/IN	通道公共端	14	1	1 通道
4	7	7 通道	13	0	0 通道
5	5	5 通道	12	3	3 通道
6	INH	使能控制	11	А	通道控制输入 A
7	VEE	模拟开关负电源	10	В	通道控制输入 B
8	VSS	电源地	9	С	通道控制输入 C



极限值

参数	符号	极限值	单位
直流电源电压	$V_{DD} - V_{SS}$	$-0.5^{\sim}18$	V
模拟电源电压	$V_{\text{DD}} - V_{\text{EE}}$	18	V
直流输入电压	V_{IN}	$-0.5 + V_{SS} \sim V_{DD} + 0.5 V$	V
功耗	PD	500	mW
工作温度	TA	$-40^{\sim}85$	°C
存储温度	Ts	-65-150	°C
引脚焊接温度	T_{W}	260, 10s	°C

注:极限参数是指无论在任何条件下都不能超过的极限值。如果超过此极限值,将有可能造成产品劣化等物理性损伤;同时在接近极限参数下,不能保证芯片可以正常工作。

原理逻辑图



真值表

	INPUTS				
INH	C	В	A	"ON" CHANNEL(S)	
0	0	0	0	0	
0	0	0	1	1	
0	0	1	0	2	
0	0	1	1	3	
0	1	0	0	4	
0	1	0	1	5	
0	1	1	0	6	
0	1	1	1	7	
1		×	×	None	

X:任意值

MSKSEMI SEMICONDUCTOR

推荐工作条件

项目	符号	最小值	典型值	最大值	单位
直流电源电压	V_{DD} - V_{SS}	3		15	V
控制输入电压	V _{IS}	0		V_{DD} - V_{SS}	V
模拟电源电压	V _{DD} -V _{EE}	0		15	V
模拟输入输出电压	V _{IN} V _{OUT}	0		V _{DD} -V _{EE}	V
工作温度	Тл	-40		85	°C

电学特性

直流电学特性: (V_{IS}=V_{IN}-V_{SS}, V_{EE}=V_{SS}, RL = 3kΩ, T_A=25℃ 除非特别指定)

符号	项目	<u>ا</u> ل	则试条件	VDD (V)	最小值	典型值	最大值	单位
		V _V		5	3.5			V
VIH	高电平有效	V _{IH} =V _{DD} through 1k	$V_{EE}=V_{SS}$,	10	7			V
	输入电压		RL=1k Ω to Vss,	15	11			V
	何中亚古社	V _{IL} =V _{DD}	$I_{\text{IS}} \leq 2uA$ on all	5			1.5	V
VIL	低电平有效	through 1k	OFF Channels	10			3	V
	输入电压			15			4	V
				5		150		
Ron	导通电阻	$0{\leqslant}V_{\text{IS}}{\leqslant}V_{\text{DD}}$		10		80		Ω
				15		60		
				5		15		
△Ron	相邻通道导通电			10		10		Ω
	阻差			15		5		
IOFF	漏电流	输入输出通道	值关闭,INH=V₪	18			± 100	nA
$I_{\rm IN}$	输入电流	$V_{\text{IN}}=V_{\text{DD}}$ or V_{SS}		18		0.01	±0.1	uA
				5		0.01	5	uA
Idd	静态电流	$V_{\text{IN}} = V_{\text{DD}}$ or V_{SS}		10		0.01	10	uA
				15		0.01	20	uA
C_{IN}	输入电容	任意输入端				5	7.5	pF
Cis	通道输入电容					5		pF
Cos	输出电容					9		pF
$C_{\rm IOS}$	导通电容					0.2		pF

交流电学特性: (Vss=VEE, Ta=25℃, tr=tf=20ns, tpd 包含 tpmL, tpLH, 见测试方法,除非特别指定

项目	符号	测试条件	VDD	最小值	典型值	最大值	单位
		V -V DI -9001-	5		15		ns
传输延迟时间	tpd	tpd V _{IS} =V _{DD} , RL=200k, CL=50pF	10		10		ns
Signal Input to Output			15		7		ns
传输延迟时间			5		100		ns
Address-to-Signal OUT	tpd		10		80		ns
(Channels ON or OFF)		RL=10k	15		50		ns



交流电学特性: (Co	ontinues,)						
项目	符号	测试条件	VDD	最小值	典型值	最大值	单位
传输延迟时间		a - a -	5		100		ns
Inhibit-to-Signal OUT	tpd	$C_L=50 \text{pF},$ $R_I=1 \text{k}$	10		50		ns
(Channel Turning ON)		KL-1K	15		30		ns
传输延迟时间		0 5 0 B	5		100		ns
Inhibit-to-Signal OUT	tpd	$C_{L}=50 \mathrm{pF},$	10		50		ns
(Channel Turning OFF)		R _L =10k	15		30		ns

测试方法









SOP-16 包装数据

单位:毫米 / 英寸



卷轴规格

P/N	PKG	QTY
74HC4051-MS	SOP-16	2500





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